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650V *e*SiC MOSFET Selection Guide 2024

Advanced Power Master Semiconductor's Silicon Carbide Technology

650V eSiC MOSFET

Smaller, Faster and More Efficient Products

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Key Features

- Extremely low switching losses
- Good FOM ; $Q_G \times R_{DS(ON)}$
- Fast intrinsic diode
- Robust Avalanche Capability

Key Benefits

- Higher System Efficiency & Reliability
- Reduced Cooling Effort
- Higher frequency applicability
- Increased power density

Applications



AI Server
PSU



xEV



Telecom/
Server PSU



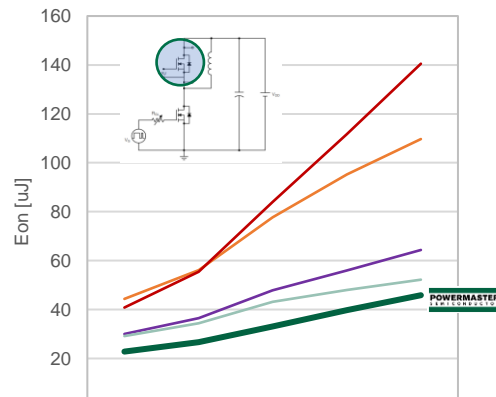
Solar
Inverter



EV Charging
Pole

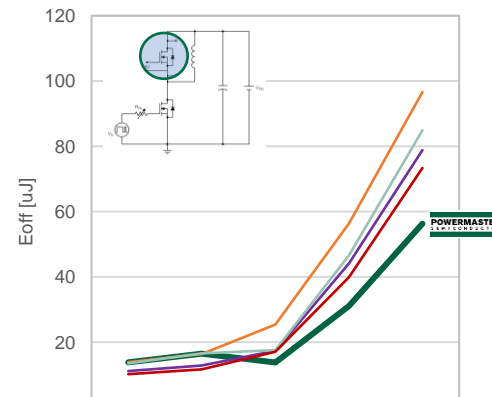
Switching Losses

Turn-on Loss



	5A	10A	20A	30A	40A
— PMS	23	27	33	40	46
— Comp. A	30	36	48	56	64
— Comp. B	44	56	78	95	110
— Comp. C	29	34	43	48	52
— Comp. D	41	55	84	112	141

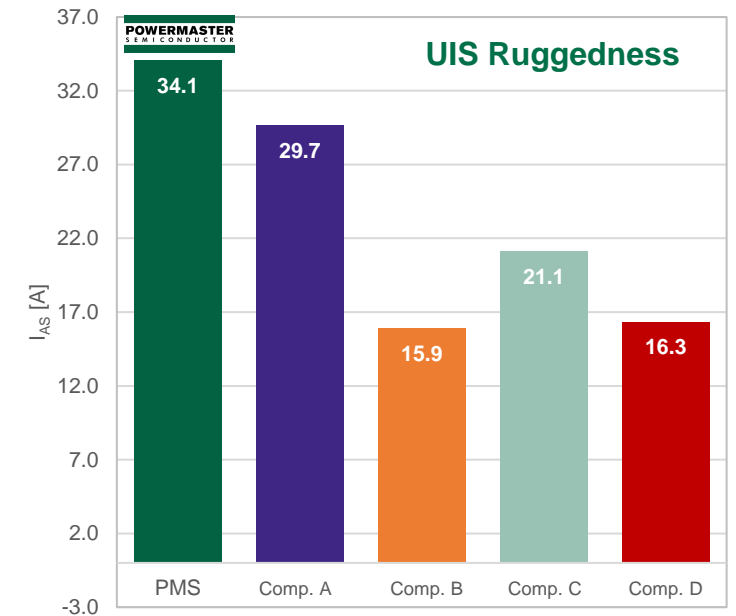
Turn-off Loss



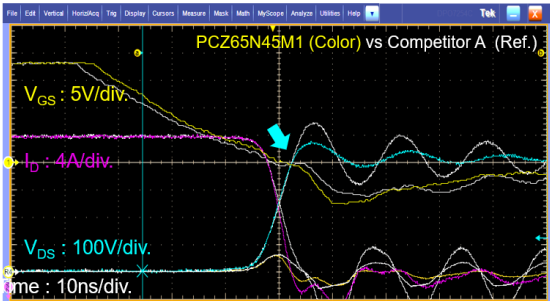
	5A	10A	20A	30A	40A
— PMS	14	17	14	31	56
— Comp. A	11	13	17	44	79
— Comp. B	14	16	25	56	97
— Comp. C	14	17	18	47	85
— Comp. D	10	12	17	40	73

Test condition : $V_{DD}=400V$, $I_D=5\sim 40A$, $V_{GS}=-3/+18V$, $R_G=2.7\Omega$, FWD : Same DUT

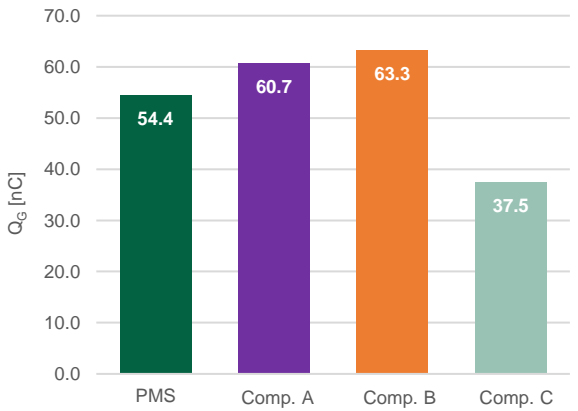
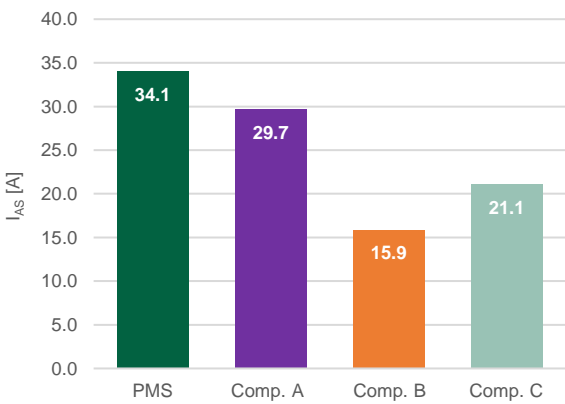
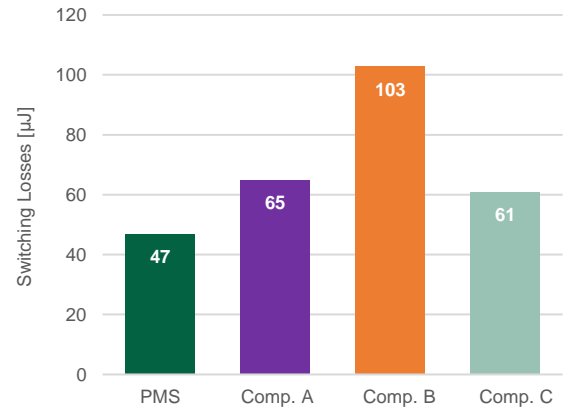
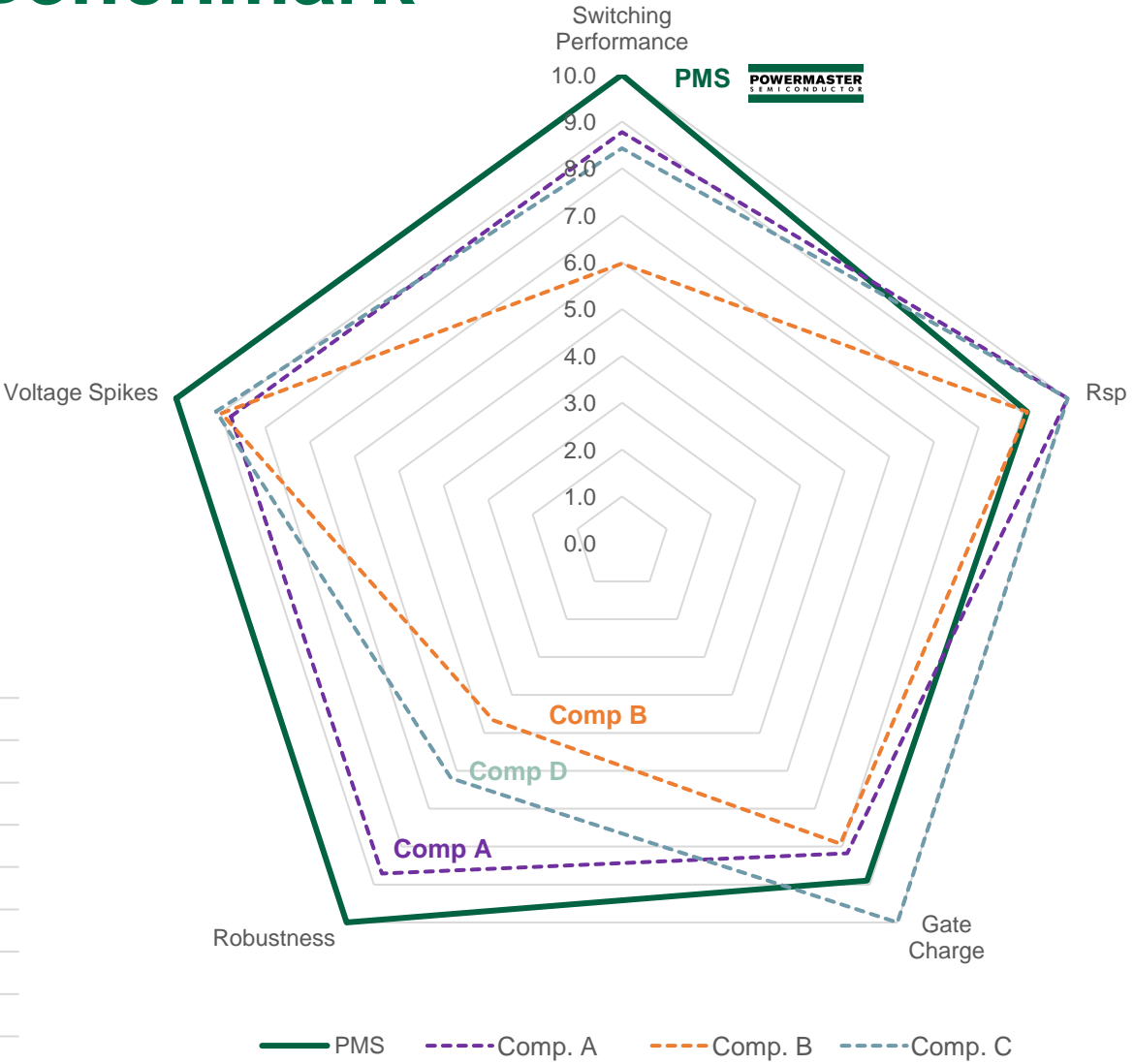
I_{AS} [A] @ L=1mH



650V / 45mΩ eSiC MOSFET PCZ65N45M1 Benchmark



Switching Performance

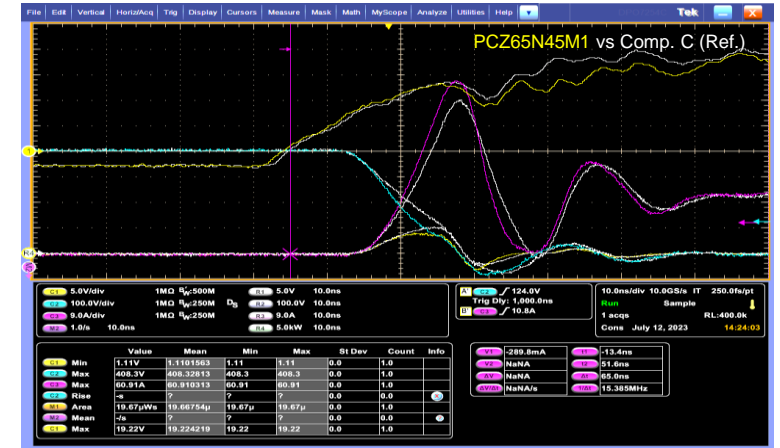
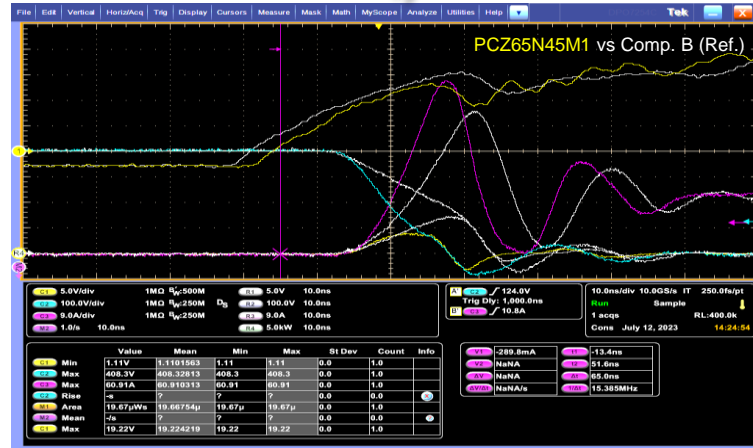
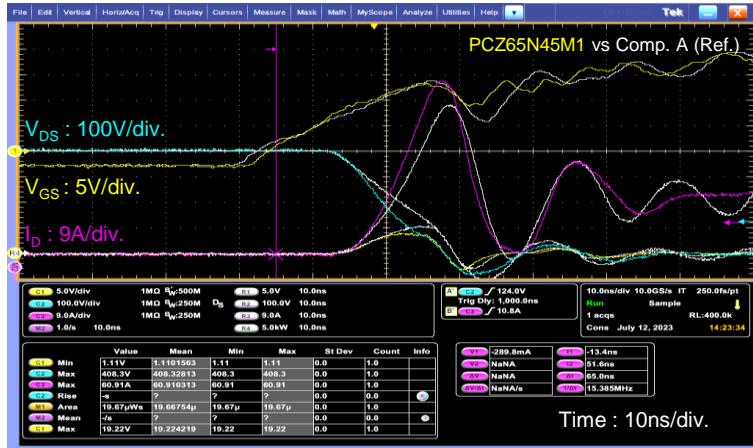


650V/45mΩ *e*SiC MOSFET Gen1

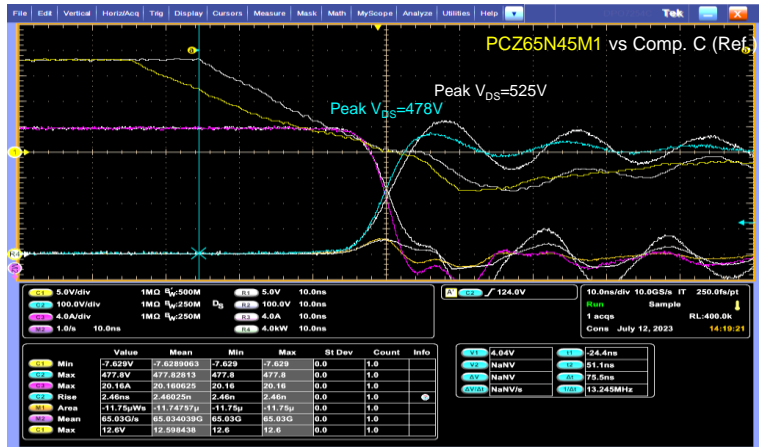
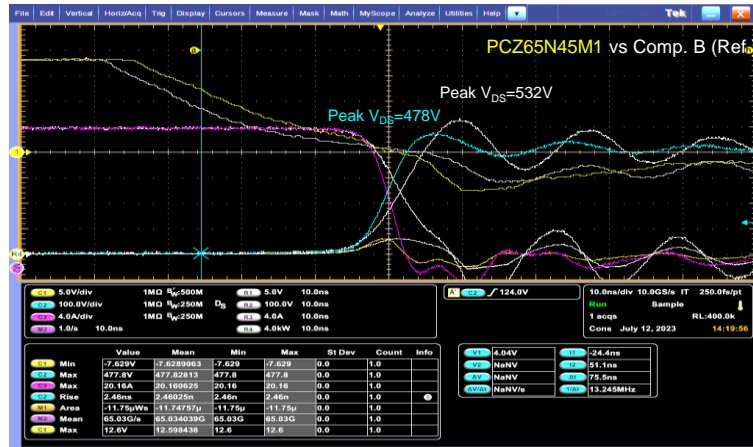
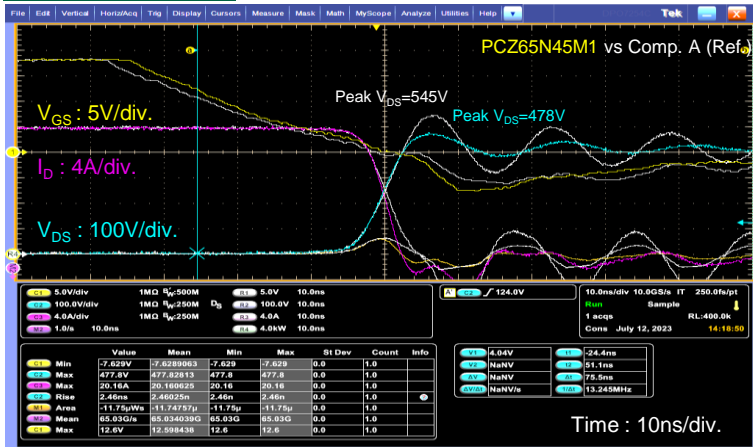
Switching Performance



Turn-on



Turn-off



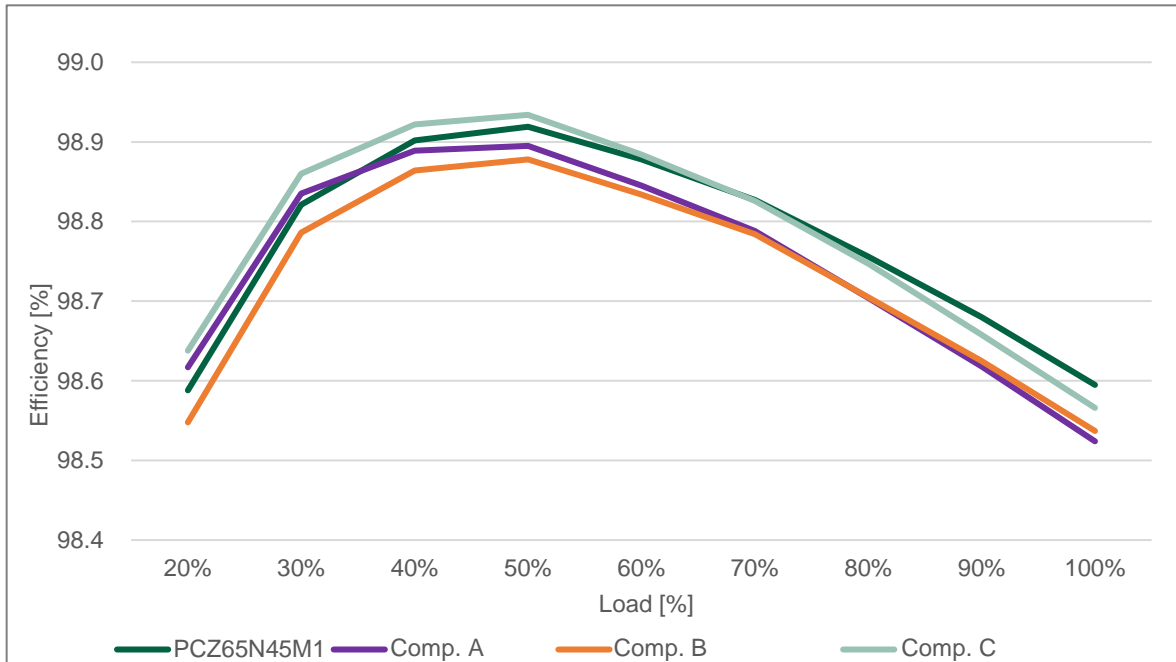
Test condition : V_{DD} =400V, I_D =5-40A, V_{GS} =-3/+18V, R_G =2.7Ω, FWD : Same DUT

650V/45mΩ *e*SiC MOSFET Gen1

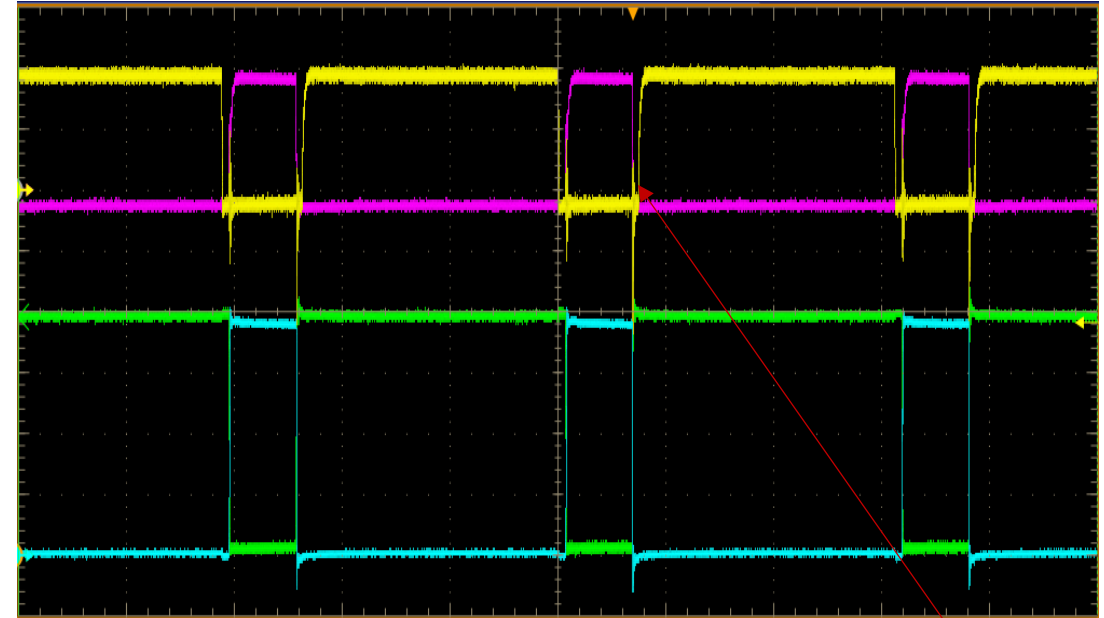
Efficiency Results @ 3kW Totem-Pole PFC



Efficiency @ 3kW Totem-pole PFC



DUT	10%	20%	30%	40%	50%	60%	70%	80%	90%	100%
PCZ65N45M1	97.66	98.59	98.82	98.90	98.92	98.88	98.83	98.76	98.68	98.60
Comp. A	97.68	98.62	98.84	98.89	98.90	98.85	98.79	98.70	98.62	98.52
Comp. B	97.63	98.55	98.79	98.86	98.88	98.83	98.78	98.71	98.63	98.54
Comp. C (Trench)	97.68	98.64	98.86	98.92	98.93	98.88	98.83	98.75	98.66	98.57



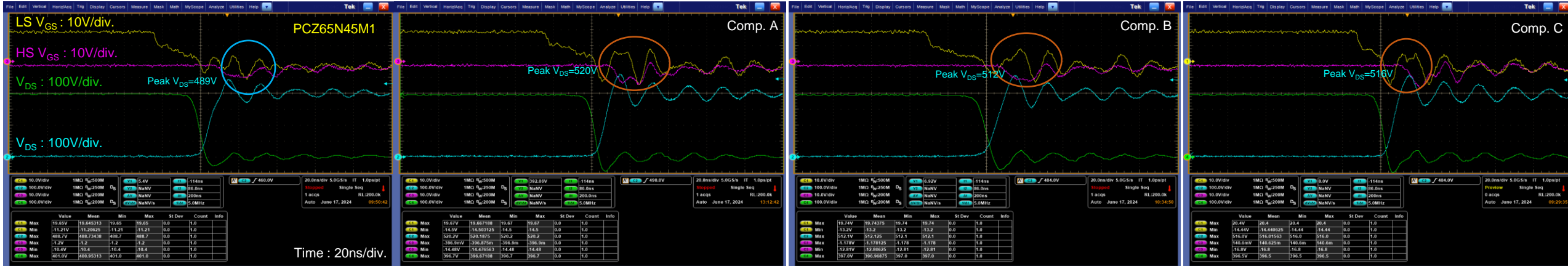
I _o =8A, 3kW	Low side - trigger			High side - trigger			Low side V _{GS} by HS MOS
	Peak V _{DS}	V _{GS} ⁻	V _{GS} ⁺	Peak V _{DS}	V _{GS} ⁻	V _{GS} ⁺	
PCZ65N45M1	489	-11.2	19.6	513	-6.0	19.2	-13.3
Comp. A	520	-14.5	19.7	541	-8.5	19.0	-26.4
Comp. B	512	-13.2	19.7	537	-6.4	18.8	-19.6
Comp. C (Trench)	516	-14.4	20.4	532	-9.6	19.3	-26.4

650V/45mΩ *e*SiC MOSFET Gen1

Switching Performance @ 3kW TP PFC



Low Side Turn-off



High Side Turn-off

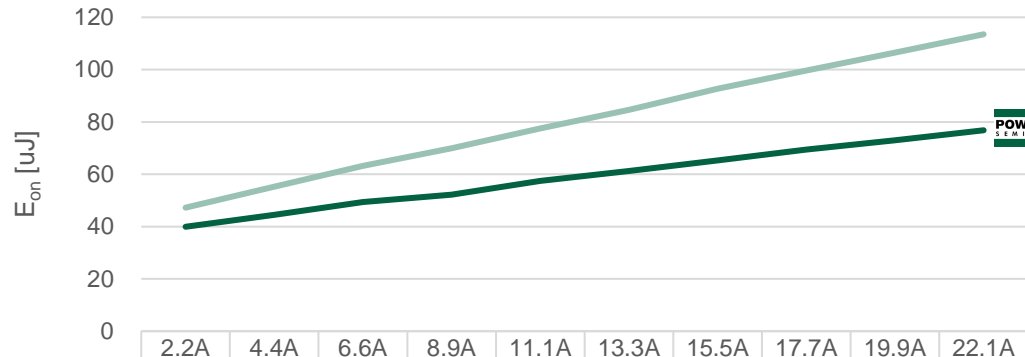


Test condition : $P_{out}=3kW$, $V_{GS}=-2.5/+18V$, $R_{ON}=22\Omega$ / $R_{ON}=4.7\Omega+1N4148$

650V/27mΩ *e*SiC MOSFET Gen1 PCT65N27M1 Switching Loss

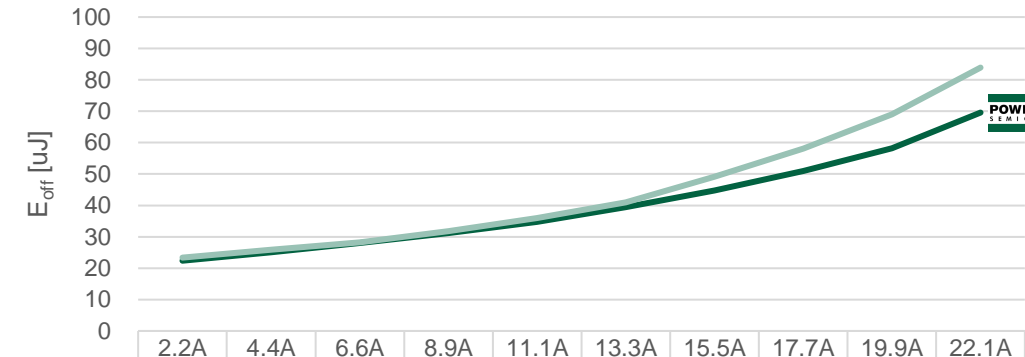


Turn-on Loss



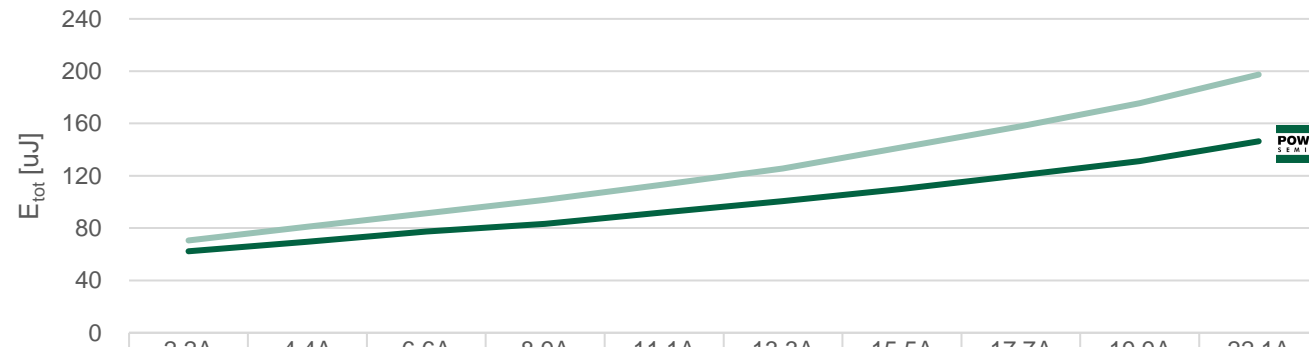
	2.2A	4.4A	6.6A	8.9A	11.1A	13.3A	15.5A	17.7A	19.9A	22.1A
— PCT65N27M1	39.9	44.4	49.4	52.1	57.4	61.2	65.3	69.4	73.0	76.8
— Best Comp.	47.2	55.3	63.2	69.9	77.5	84.6	92.6	99.7	106.5	113.5

Turn-off Loss



	2.2A	4.4A	6.6A	8.9A	11.1A	13.3A	15.5A	17.7A	19.9A	22.1A
— PCT65N27M1	22.4	25.1	28.1	31.2	34.8	39.4	44.8	51.0	58.2	69.6
— Best Comp.	23.4	25.9	28.2	31.8	36.0	41.0	49.1	58.1	69.0	83.9

Total SW Loss

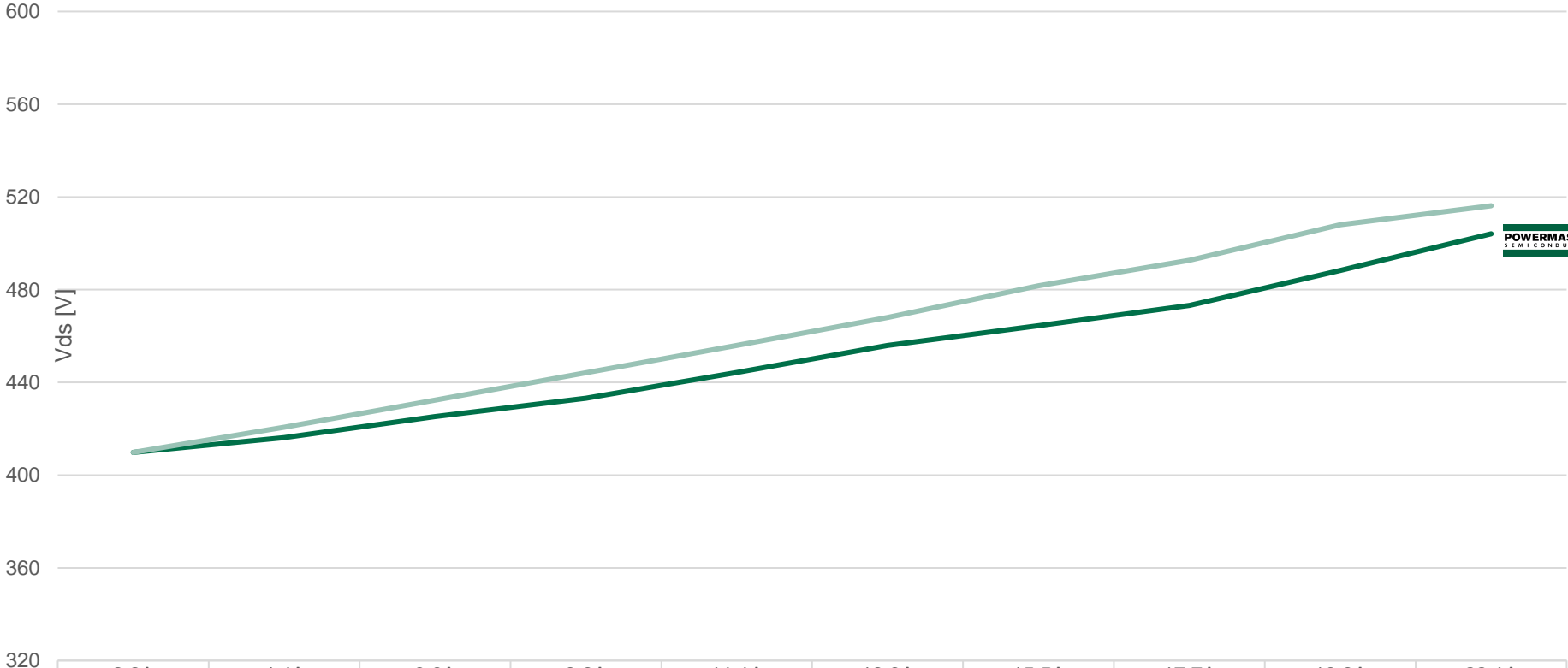


	2.2A	4.4A	6.6A	8.9A	11.1A	13.3A	15.5A	17.7A	19.9A	22.1A
— PCT65N27M1	62.3	69.5	77.5	83.3	92.2	100.6	110.1	120.4	131.2	146.4
— Best Comp.	70.6	81.2	91.4	101.7	113.4	125.6	141.7	157.8	175.5	197.4

650V/27mΩ *e*SiC MOSFET Gen1 PCT65N27M1 Switching Noise



Spike of Drain Voltage @ Turn-off



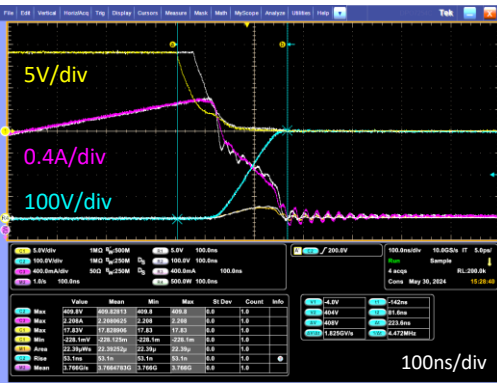
	2.2A	4.4A	6.6A	8.9A	11.1A	13.3A	15.5A	17.7A	19.9A	22.1A
— PCT65N27M1	410	416	425	433	444	456	465	473	488	504
— Best Comp.	410	421	432	444	456	468	482	493	508	516

V_{DD}=800V, V_{GS}=-3V/+18V, Ext R_g=4.7Ω, FWD=PCH120S20D1

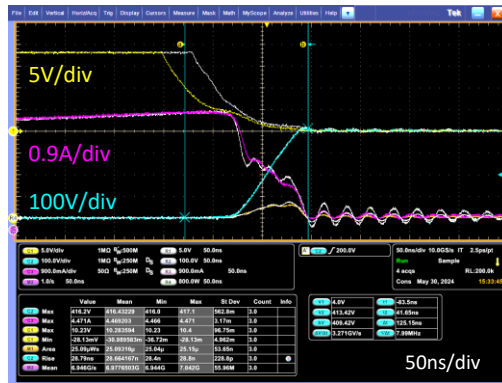
650V/27mΩ *e*SiC MOSFET Gen1 PCT65N27M1 Turn-off Switching Waveforms



2.21A



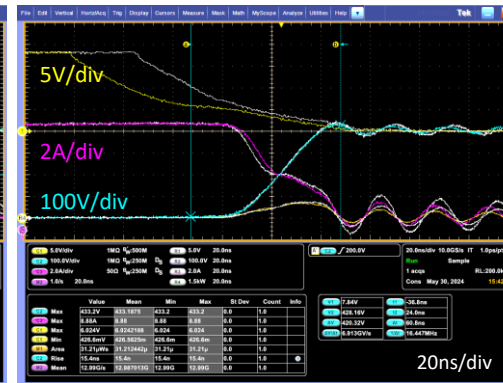
4.43A



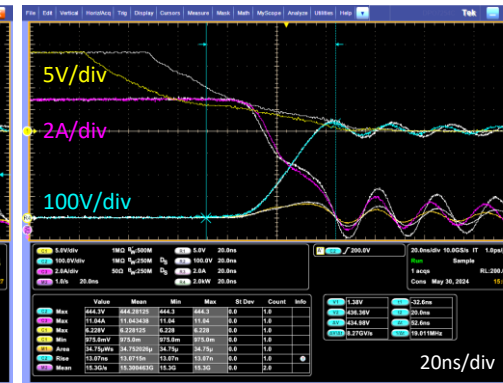
6.64A



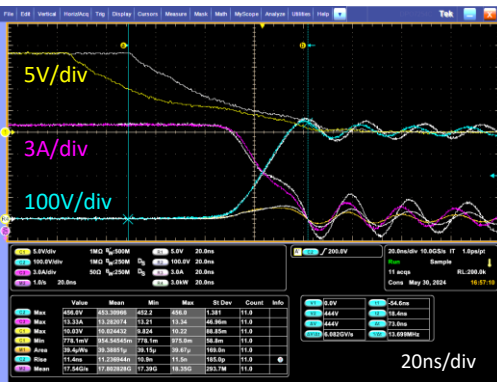
8.85A



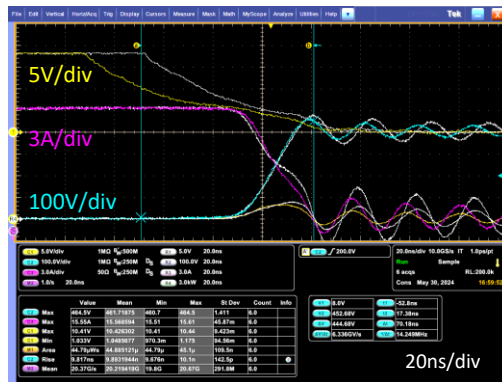
11.07A



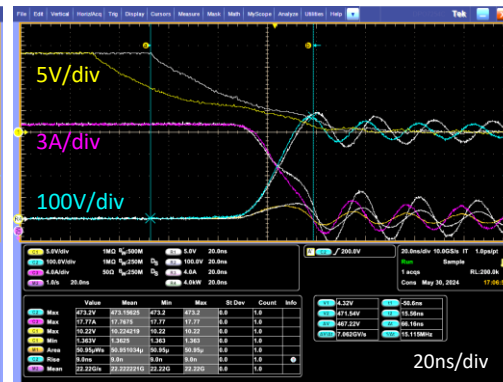
13.28A



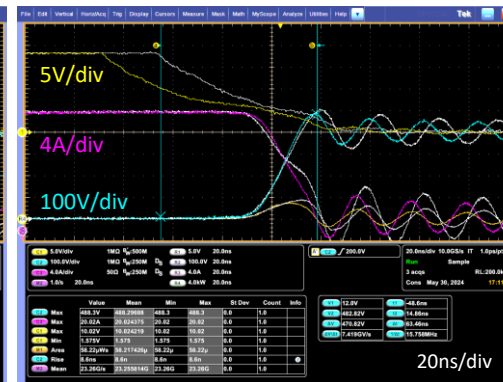
15.49A



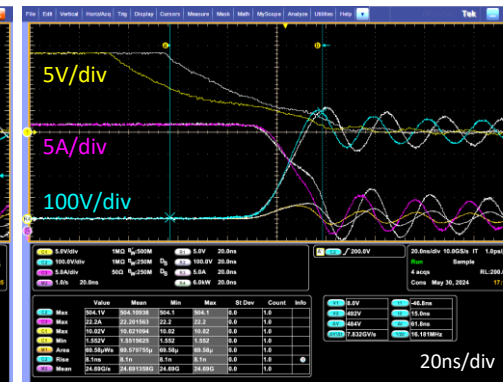
17.71A



19.92A



22.14A



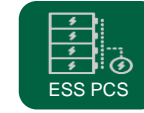
Color : PCT65N27M1
Ref. : Best Comp.

$V_{DD}=800V$, $V_{GS}=-3V/+18V$, Ext Rg=4.7Ω, FWD=PCH120S20D1

650V *e*SiC MOSFET Gen1. Portfolio

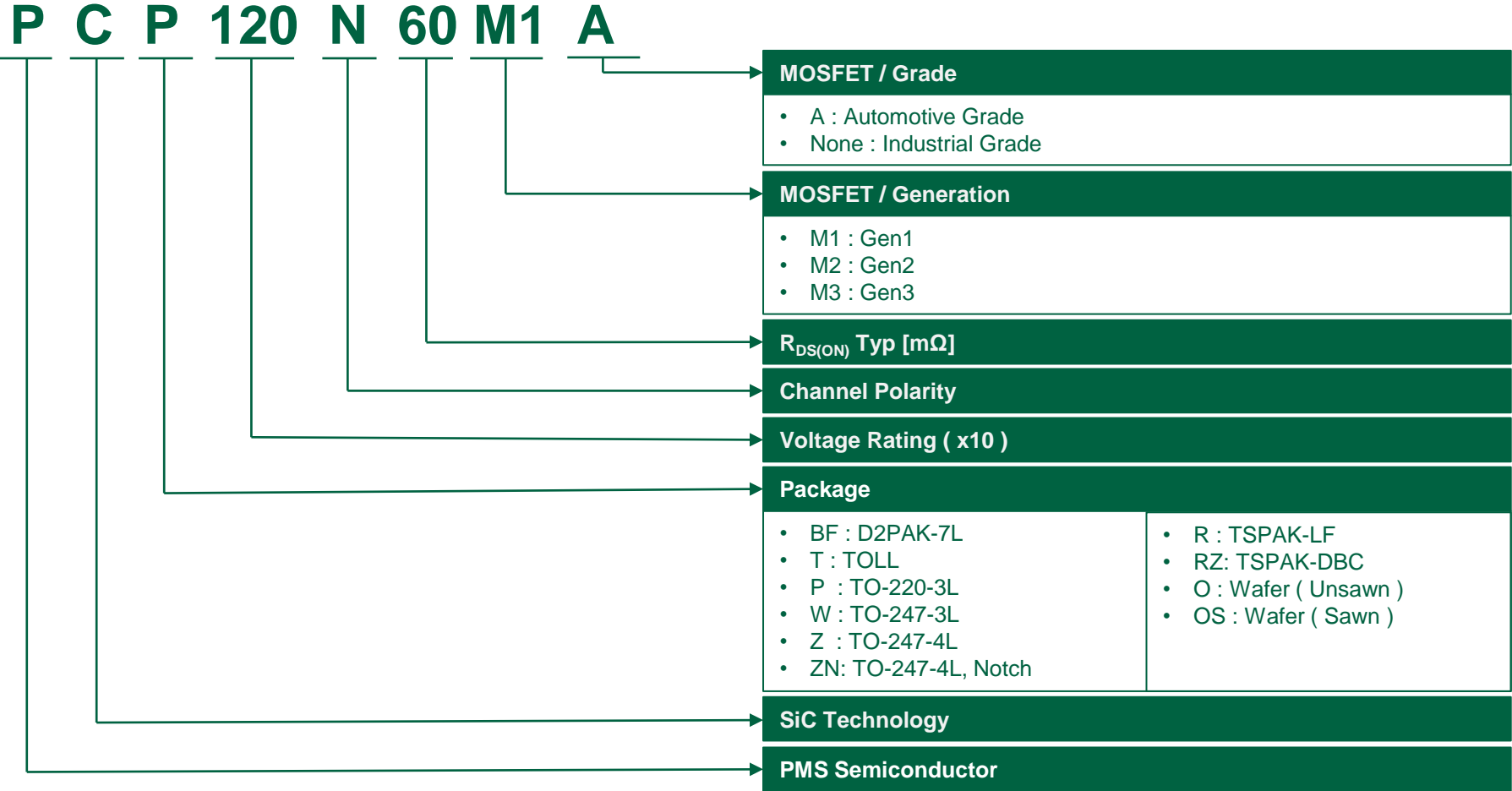
Available now

On Planning [Release Target]



Package $R_{DS(ON)}_{typ}$	Bare Die	TOLL	D2PAK-7L	TO-247-3L	TO-247-4L
15mΩ	PCO65N15M1	PCT65N15M1	PCBF65N15M1	PCW65N15M1	PCZ65N15M1
22mΩ	PCO65N22M1	PCT65N22M1			
27mΩ	PCO65N27M1	PCT65N27M1	PCBF65N27M1	PCW65N27M1	PCZ65N27M1
39mΩ	PCO65N39M1	PCT65N39M1			
45mΩ	PCO65N45M1	PCT65N45M1	PCBF65N45M1	PCW65N45M1	PCZ65N45M1

Ordering System (SiC MOSFET)



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